



50V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	Rds(on)	I _D T _A = +25°C
50V	1.6Ω @ $V_{GS} = 10V$	0.46A
	2.5Ω @ V _{GS} = 4.5V	0.36A

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN53D0LDWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

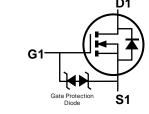
Mechanical Data

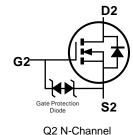
- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208[®]
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

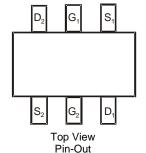




Top View







Ordering Information (Note 4)

Part Number	Case	Packaging
DMN53D0LDWQ-7	SOT363	3000/Tape & Reel
DMN53D0LDWQ-13	SOT363	10000/Tape & Reel

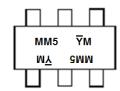
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

Q1 N-Channel

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \text{MM5} = \text{Product Type Marking Code} \\ \overline{\text{Y}} \text{M} = \text{Date Code Marking} \\ \overline{\text{Y}} = \text{Year (ex: H} = 2020) \\ \text{M} = \text{Month (ex: 9} = \text{September)} \end{array}$

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н		J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	50	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6), V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	0.46 0.37	А
Pulsed Drain Current (10µs Pulse, 1% Duty Cyc	le)	I _{DM}	1	A	
Maximum Continuous Body Diode Forward Curr	ent (Note 6)	Maximum Continuous Body Diode Forward Current (Note 6)			

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

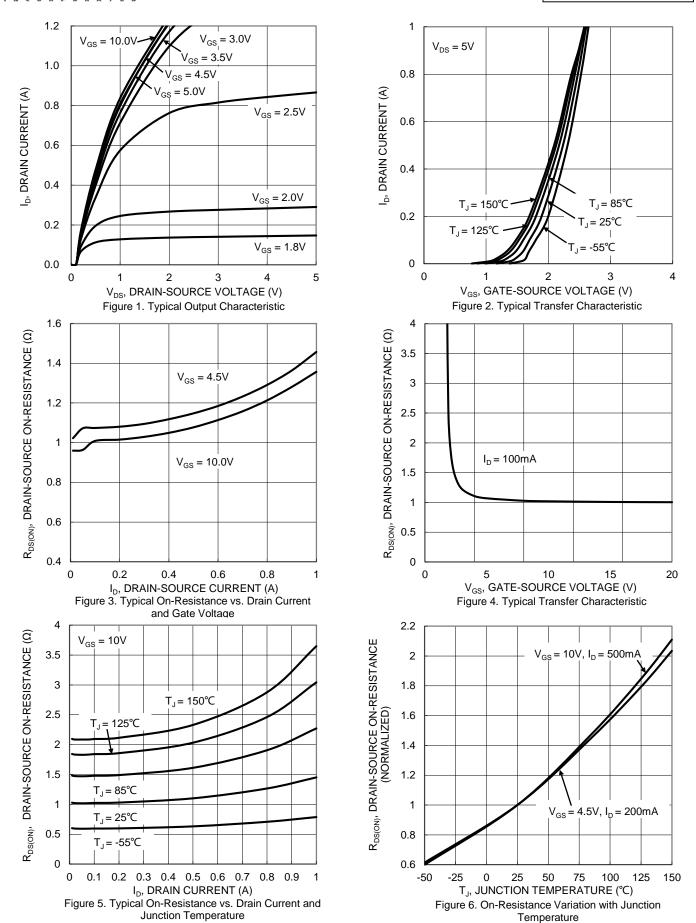
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		Po	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	317.6	°C/W
Total Power Dissipation (Note 6)		Po	0.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	249.8	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	50		1	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_		1.0	μA	V _{DS} = 50V, V _{GS} = 0V	
Gate-Body Leakage	Igss	_	_	10	μA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	0.8	_	1.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_	1.0	1.6		$V_{GS} = 10V, I_D = 500mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.0	2.5	Ω	$V_{GS} = 4.5V, I_D = 200mA$	
			1.4	4.5		V _G S = 2.5V, I _D = 100mA	
Source-Drain Diode Forward Voltage	VsD	_	0.8	1.4	V	$V_{GS} = 0V$, $I_{S} = 500mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	49.5	_			
Output Capacitance	Coss	_	5.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	3.7	_		1 = 1.0WHZ	
Gate Resistance	Rg		53		Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$	
Total Gate Charge V _{GS} = 10V	Qg	1	1.4	1			
Total Gate Charge V _{GS} = 4.5V	Qg	1	0.7	1	nC	V _{DS} = 10V, I _D = 250mA	
Gate-Source Charge	Qgs	1	0.2	1	110	$VDS = 10V, I_D = 250IIIA$	
Gate-Drain Charge	Q_{gd}	_	0.1	_			
Turn-On Delay Time	td(on)	1	3.7	-			
Turn-On Rise Time	t _R	1	1.6		no	V _{DD} = 30V, V _{GS} = 10V,	
Turn-Off Delay Time	tD(OFF)		18.7	_	ns	$R_G = 25\Omega$, $I_D = 200mA$	
Turn-Off Fall Time	tF		7.0	_			

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.









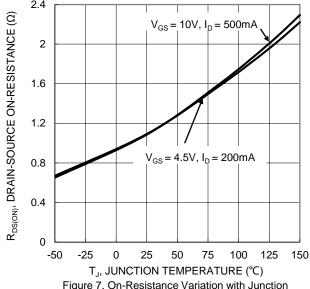


Figure 7. On-Resistance Variation with Junction Temperature

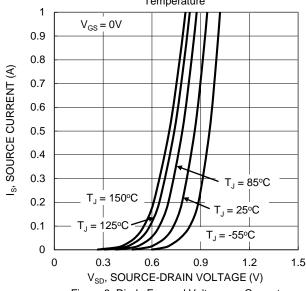
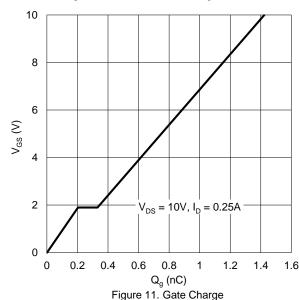
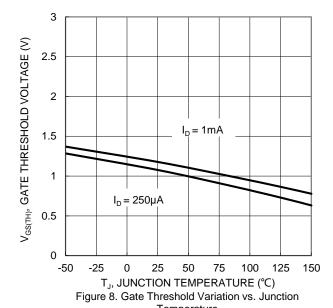
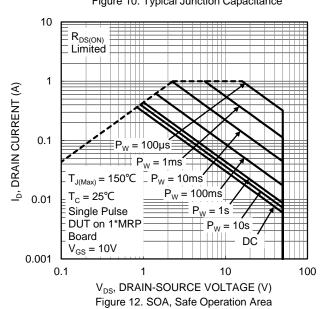


Figure 9. Diode Forward Voltage vs. Current





Temperature 100 f = 1MHz C_T, JUNCTION CAPACITANCE (pF) $\boldsymbol{C}_{\text{iss}}$ 10 Coss Crss 1 0 10 20 30 40 50 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance





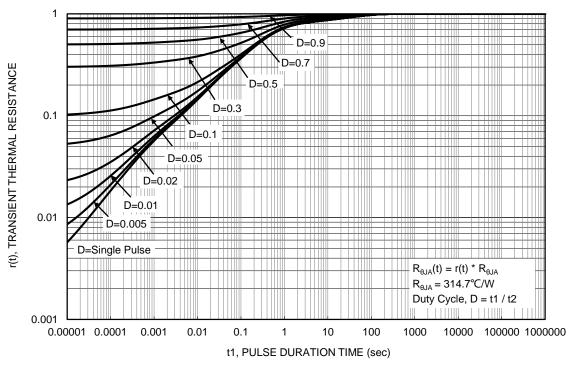


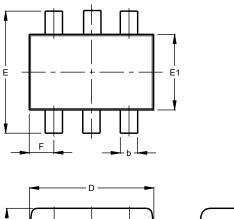
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



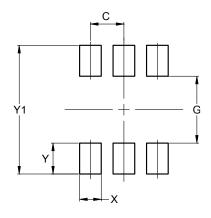
-	D	
A2		
	┫ ┩	a

SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
C	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	C	.650 E	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All I	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2 500



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